



# BUK9K6R2-40E

Dual N-channel TrenchMOS logic level FET

23 April 2013

Product data sheet

## 1. General description

Dual logic level N-channel MOSFET in a LFPAK56D package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

## 2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with  $V_{GS(th)} > 0.5$  V @ 175 °C

## 3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

## 4. Quick reference data

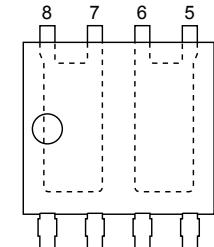
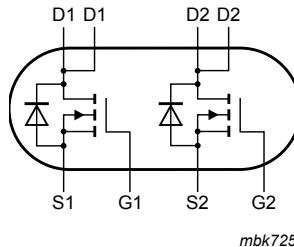
Table 1. Quick reference data

| Symbol                                       | Parameter                        | Conditions   |  | Min | Typ  | Max | Unit      |
|--|----------------------------------|--|--|-----|------|-----|-----------|
| $V_{DS}$                                     | drain-source voltage             | $T_j \geq 25$ °C; $T_j \leq 175$ °C  |  | -   | -    | 40  | V         |
| $I_D$  | drain current                    | $V_{GS} = 5$ V; $T_{mb} = 25$ °C; <a href="#">Fig. 1</a>   |  | -   | -    | 40  | A         |
| $P_{tot}$                                    | total power dissipation          | $T_{mb} = 25$ °C; <a href="#">Fig. 2</a>   |  | -   | -    | 68  | W         |
| <b>Static characteristics FET1 and FET2</b>  |                                  |  |  |     |      |     |           |
| $R_{DSon}$                                   | drain-source on-state resistance | $V_{GS} = 5$ V; $I_D = 20$ A; $T_j = 25$ °C; <a href="#">Fig. 12</a>   |  | -   | 5.27 | 6.2 | $m\Omega$ |
| <b>Dynamic characteristics FET1 and FET2</b> |                                  |  |  |     |      |     |           |
| $Q_{GD}$                                     | gate-drain charge                | $I_D = 10$ A; $V_{DS} = 32$ V; $V_{GS} = 10$ V; $T_j = 25$ °C; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a> |  | -   | 5.8  | -   | nC        |

**nexperia**

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline  | Graphic symbol  |
|-----|--------|-------------|---|---|
| 1   | S1     | source1     |   |   |
| 2   | G1     | gate1       |   |   |
| 3   | S2     | source2     |   |   |
| 4   | G2     | gate2       |   |   |
| 5   | D2     | drain2      |   |   |
| 6   | D2     | drain2      |   |   |
| 7   | D1     | drain1      |   |   |
| 8   | D1     | drain1      | <br>LFPAK56D (SOT1205) | <br>mbk725 |

## 6. Ordering information

Table 3. Ordering information

| Type number  | Package  |  |         |
|--------------|----------|--|---------|
|              | Name     | Description  | Version |
| BUK9K6R2-40E | LFPAK56D | Plastic single ended surface mounted package (LFPAK56D); 8 leads | SOT1205 |

## 7. Marking

Table 4. Marking codes

| Type number  | Marking code |
|--------------|--------------|
| BUK9K6R2-40E | 96E240       |

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol    | Parameter            | Conditions  | Min | Max | Unit |
|-----------|----------------------|---|-----|-----|------|
| $V_{DS}$  | drain-source voltage | $T_j \geq 25^\circ\text{C}$ ; $T_j \leq 175^\circ\text{C}$                                      | -   | 40  | V    |
| $V_{DGR}$ | drain-gate voltage   | $R_{GS} = 20\text{ k}\Omega$ ; $T_j \geq 25^\circ\text{C}$ ; $T_j \leq 175^\circ\text{C}$       | -   | 40  | V    |
| $V_{GS}$  | gate-source voltage  | $T_j \leq 175^\circ\text{C}$ ; DC   | -10 | 10  | V    |
|           |                      | $T_j \leq 175^\circ\text{C}$ ; Pulsed   |     |     |      |
| $I_D$     | drain current        | $T_{mb} = 25^\circ\text{C}$ ; $V_{GS} = 5\text{ V}$ ; <a href="#">Fig. 1</a>                    | -40 | 40  | A    |
|           |                      | $T_{mb} = 100^\circ\text{C}$ ; $V_{GS} = 5\text{ V}$ ; <a href="#">Fig. 1</a>                   |     |     |      |
| $I_{DM}$  | peak drain current   | $T_{mb} = 25^\circ\text{C}$ ; pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; <a href="#">Fig. 4</a> | -   | 295 | A    |

| Symbol       | Parameter                  | Conditions   | Min | Max | Unit |
|--------------|----------------------------|--|-----|-----|------|
| $P_{tot}$    | total power dissipation    | $T_{mb} = 25^\circ\text{C}$ ; <a href="#">Fig. 2</a> | -   | 68  | W    |
| $T_{stg}$    | storage temperature        |  | -55 | 175 | °C   |
| $T_j$        | junction temperature       |  | -55 | 175 | °C   |
| $T_{sld(M)}$ | peak soldering temperature |  | -   | 260 | °C   |

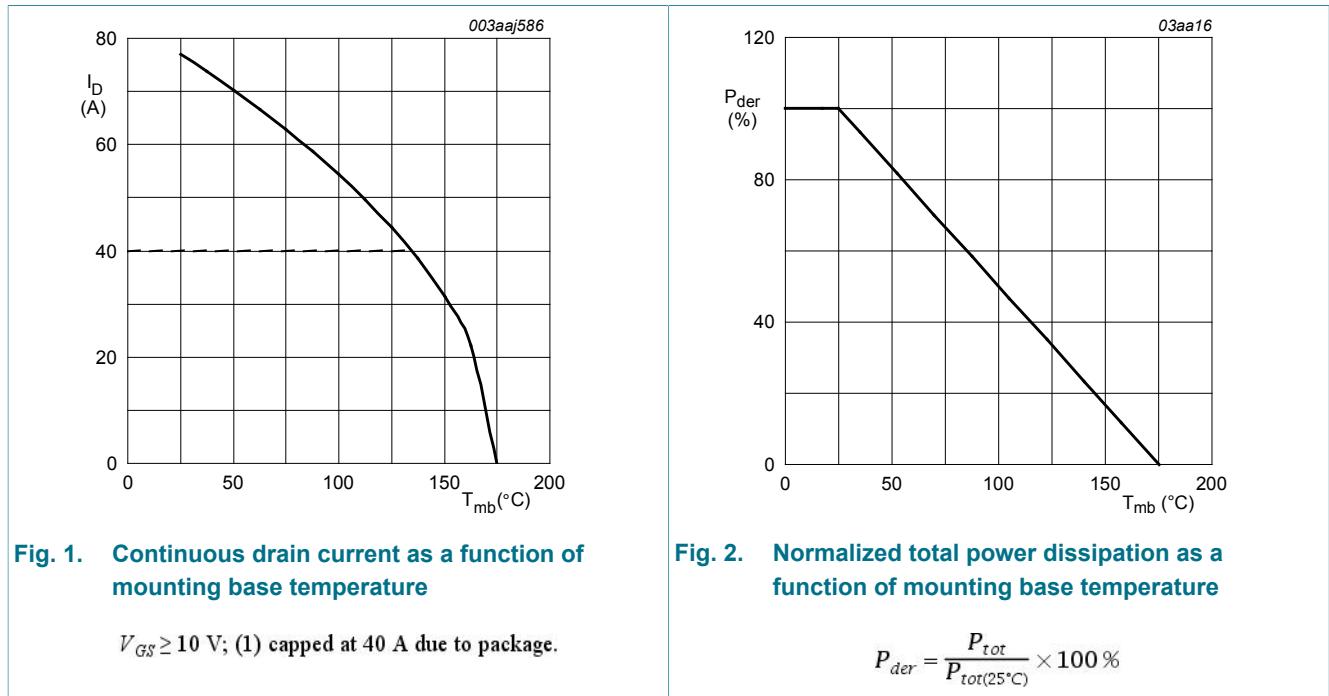
**Source-drain diode FET1 and FET2**

|          |                     |   |   |     |   |
|----------|---------------------|---|---|-----|---|
| $I_S$    | source current      | $T_{mb} = 25^\circ\text{C}$                                     | - | 40  | A |
| $I_{SM}$ | peak source current | pulsed; $t_p \leq 10 \mu\text{s}$ ; $T_{mb} = 25^\circ\text{C}$ | - | 295 | A |

**Avalanche Ruggedness FET1 and FET2**

|               |  |   |        |   |     |    |
|---------------|--|---|--------|---|-----|----|
| $E_{DS(AL)S}$ | non-repetitive drain-source avalanche energy | $I_D = 40 \text{ A}$ ; $V_{sup} \leq 40 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; $T_{j(\text{init})} = 25^\circ\text{C}$ ; <a href="#">Fig. 3</a> | [3][4] | - | 166 | mJ |
|---------------|--|---|--------|---|-----|----|

- [1] Accumulated Pulse duration up to 50 hours delivers zero defect ppm
- [2] Significantly longer life times are achieved by lowering  $T_j$  and or  $V_{GS}$ .
- [3] Refer to application note AN10273 for further information
- [4] Single-pulse avalanche rating limited by maximum junction temperature of  $175^\circ\text{C}$



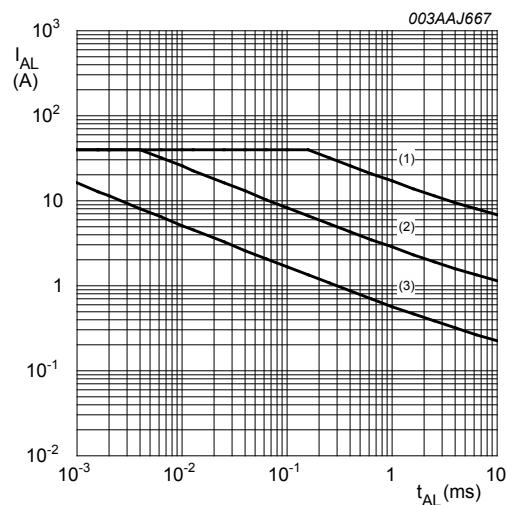


Fig. 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time, FET1 and FET2

- (1) Single-pulse;  $T_j = 25^\circ\text{C}$ .
- (2) Single-pulse;  $T_j = 150^\circ\text{C}$ .
- (3) Repetitive.

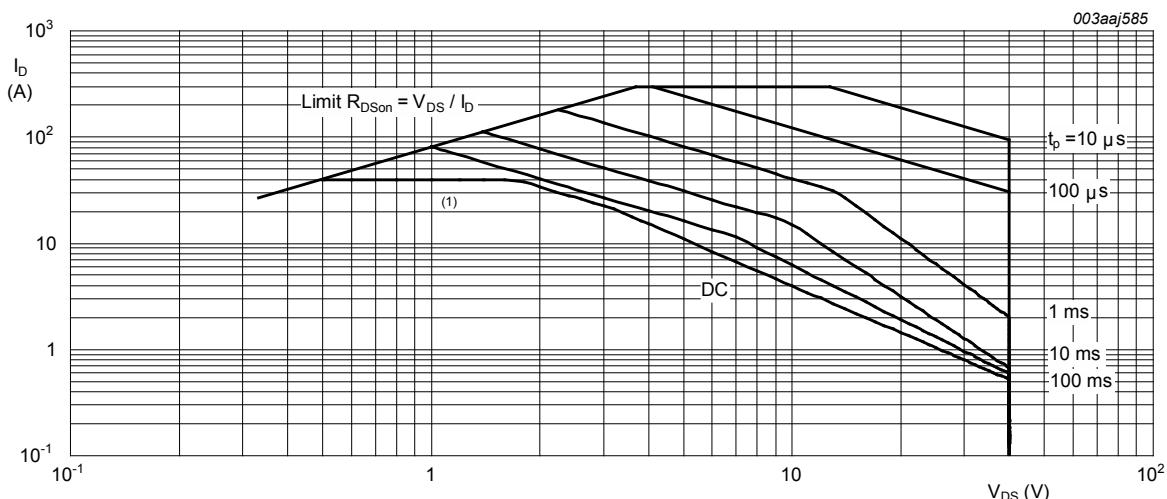


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

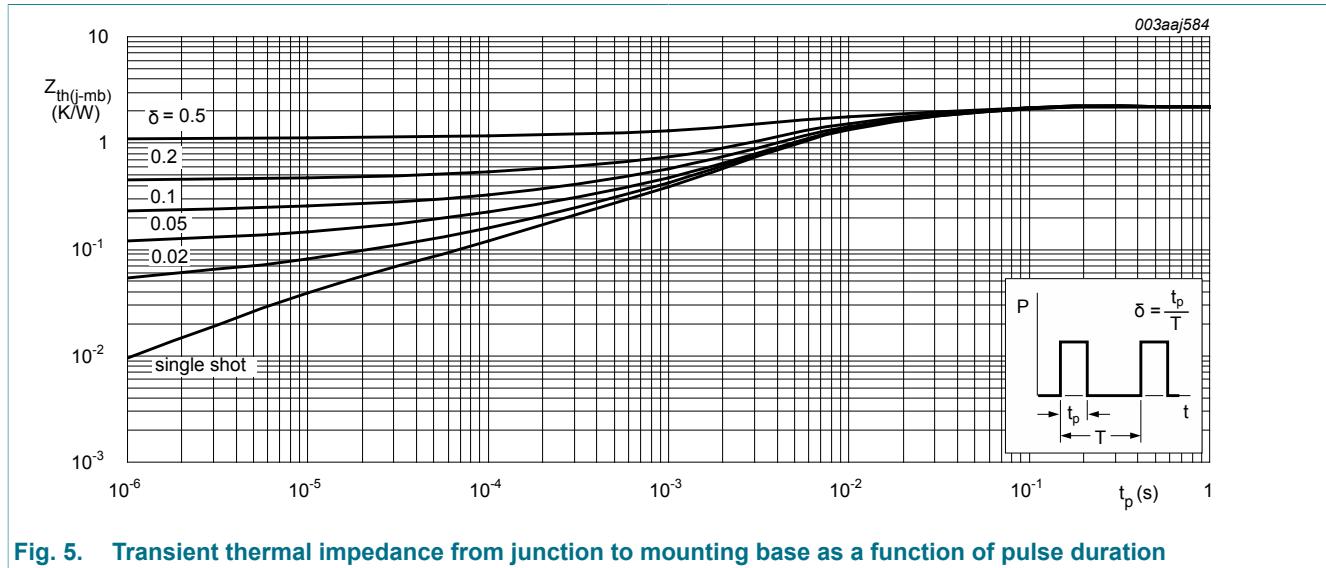
$T_{mb} = 25^\circ\text{C}$ ;  $I_{DM}$  is a single pulse; (1) Capped at 40 A due to package

## 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter   | Conditions             |  | Min | Typ | Max  | Unit |
|----------------|---|------------------------|--|-----|-----|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | <a href="#">Fig. 5</a> |  | -   | -   | 2.21 | K/W  |

| Symbol        | Parameter                                   | Conditions  |  | Min | Typ | Max | Unit |
|---------------|---|---|--|-----|-----|-----|------|
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | Minimum footprint; mounted on a printed circuit board |  | -   | 95  | -   | K/W  |



## 10. Characteristics

Table 7. Characteristics

| Symbol                                      | Parameter                        | Conditions  |  | Min | Typ  | Max  | Unit      |
|---|----------------------------------|---|--|-----|------|------|-----------|
| <b>Static characteristics FET1 and FET2</b> |                                  |   |  |     |      |      |           |
| $V_{(BR)DSS}$                               | drain-source breakdown voltage   | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55^\circ C$  |  | 36  | -    | -    | V         |
|   |                                  | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25^\circ C$   |  | 40  | -    | -    | V         |
| $V_{GS(th)}$                                | gate-source threshold voltage    | $I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25^\circ C$<br><a href="#">Fig. 10</a> ; <a href="#">Fig. 11</a>  |  | 1.4 | 1.7  | 2.1  | V         |
|   |                                  | $I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175^\circ C$<br><a href="#">Fig. 10</a> ; <a href="#">Fig. 11</a> |  | 0.5 | -    | -    | V         |
|   |                                  | $I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55^\circ C$<br><a href="#">Fig. 10</a> ; <a href="#">Fig. 11</a> |  | -   | -    | 2.45 | V         |
| $I_{DSS}$                                   | drain leakage current            | $V_{DS} = 40 V; V_{GS} = 0 V; T_j = 175^\circ C$  |  | -   | -    | 500  | $\mu A$   |
|   |                                  | $V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25^\circ C$   |  | -   | 0.02 | 1    | $\mu A$   |
| $I_{GSS}$                                   | gate leakage current             | $V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25^\circ C$  |  | -   | 2    | 100  | nA        |
|   |                                  | $V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25^\circ C$   |  | -   | 2    | 100  | nA        |
| $R_{DSon}$                                  | drain-source on-state resistance | $V_{GS} = 5 V; I_D = 20 A; T_j = 25^\circ C$ ; <a href="#">Fig. 12</a>                                |  | -   | 5.27 | 6.2  | $m\Omega$ |
|   |                                  | $V_{GS} = 5 V; I_D = 20 A; T_j = 175^\circ C$ ; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>     |  | -   | 10.2 | 12.5 | $m\Omega$ |

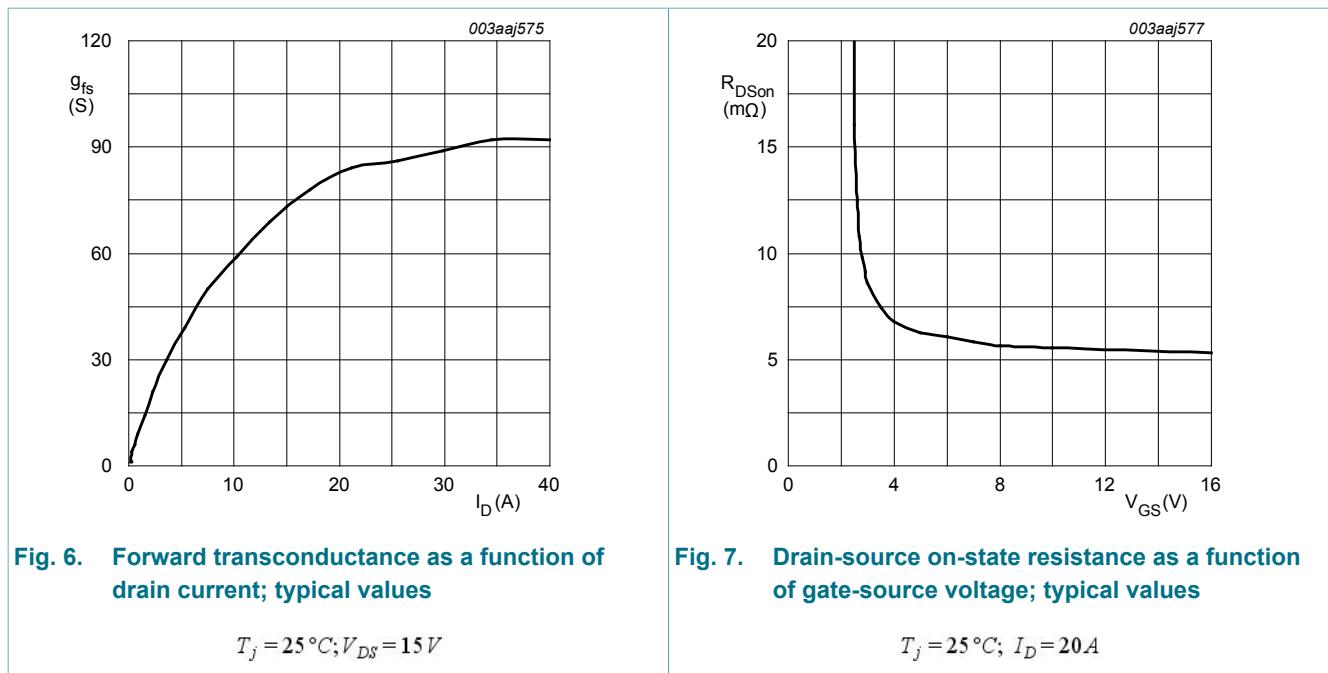
| Symbol | Parameter | Conditions  |  | Min | Typ  | Max | Unit             |
|--------|-----------|---|--|-----|------|-----|------------------|
|        |           | $V_{GS} = 10 \text{ V}$ ; $I_D = 20 \text{ A}$ ; $T_j = 25 \text{ }^\circ\text{C}$ ;<br><a href="#">Fig. 12</a> |  | -   | 4.84 | 6   | $\text{m}\Omega$ |

**Dynamic characteristics FET1 and FET2**

|                     |                              |   |  |   |      |      |    |
|---------------------|------------------------------|---|--|---|------|------|----|
| $Q_{G(\text{tot})}$ | total gate charge            | $I_D = 10 \text{ A}$ ; $V_{DS} = 32 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ;<br>$T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>   |  | - | 35.4 | -    | nC |
| $Q_{GS}$            | gate-source charge           |   |  | - | 4.4  | -    | nC |
| $Q_{GD}$            | gate-drain charge            |   |  | - | 5.8  | -    | nC |
| $C_{iss}$           | input capacitance            | $V_{GS} = 0 \text{ V}$ ; $V_{DS} = 25 \text{ V}$ ; $f = 1 \text{ MHz}$ ;<br>$T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 16</a>                               |  | - | 2461 | 3281 | pF |
| $C_{oss}$           | output capacitance           |   |  | - | 345  | 414  | pF |
| $C_{rss}$           | reverse transfer capacitance |   |  | - | 162  | 222  | pF |
| $t_{d(\text{on})}$  | turn-on delay time           | $V_{DS} = 32 \text{ V}$ ; $R_L = 3.3 \Omega$ ; $V_{GS} = 10 \text{ V}$ ;<br>$R_{G(\text{ext})} = 5 \Omega$ ; $T_j = 25 \text{ }^\circ\text{C}$ ; $I_D = 10 \text{ A}$ |  | - | 6    | -    | ns |
| $t_r$               | rise time                    |   |  | - | 7.1  | -    | ns |
| $t_{d(\text{off})}$ | turn-off delay time          |   |  | - | 44.4 | -    | ns |
| $t_f$               | fall time                    |   |  | - | 19.8 | -    | ns |

**Source-drain diode FET1 and FET2**

|          |                       |   |  |   |      |     |    |
|----------|-----------------------|---|--|---|------|-----|----|
| $V_{SD}$ | source-drain voltage  | $I_S = 15 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 17</a> |  | - | 0.78 | 1.2 | V  |
| $t_{rr}$ | reverse recovery time | $I_S = 10 \text{ A}$ ; $dI_S/dt = -100 \text{ A}/\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ;                    |  | - | 23.7 | -   | ns |
| $Q_r$    | recovered charge      | $V_{DS} = 20 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$   |  | - | 16.8 | -   | nC |



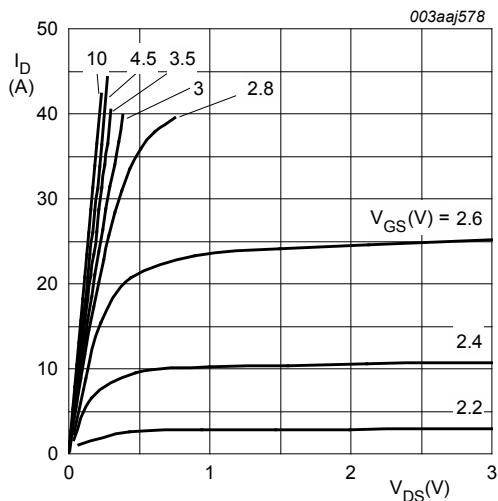


Fig. 8. Output characteristics: drain current as a function of drain-source voltage; typical values

$T_j = 25^\circ\text{C}$

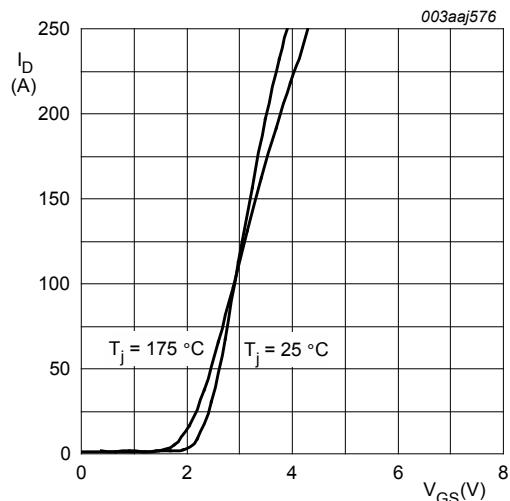


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$V_{DS} = 10\text{V}$

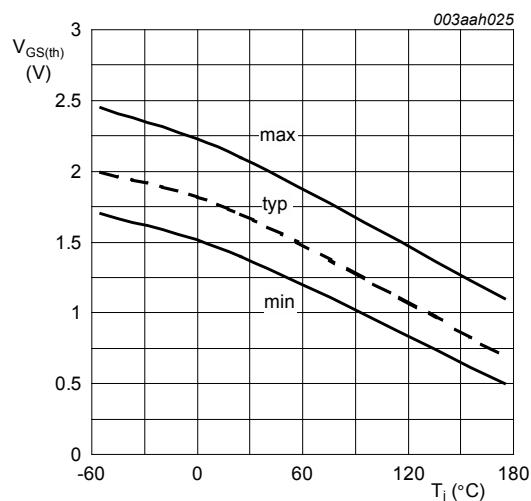


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

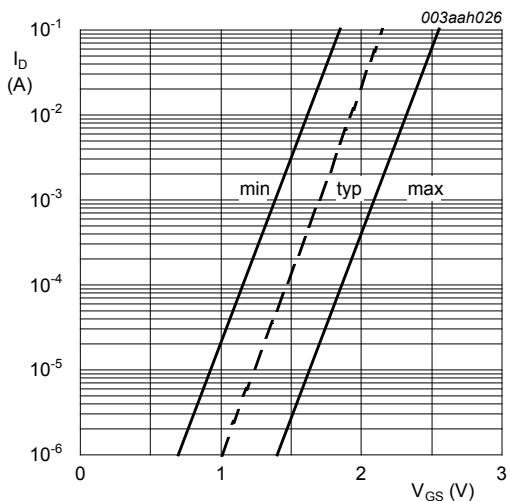
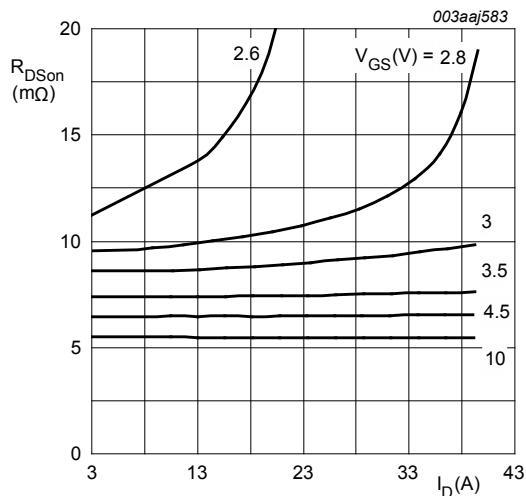


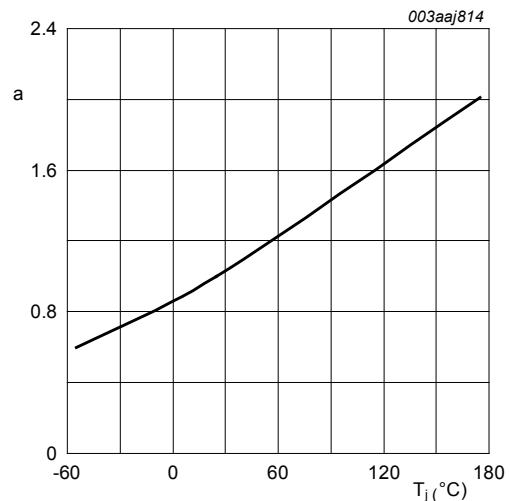
Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$



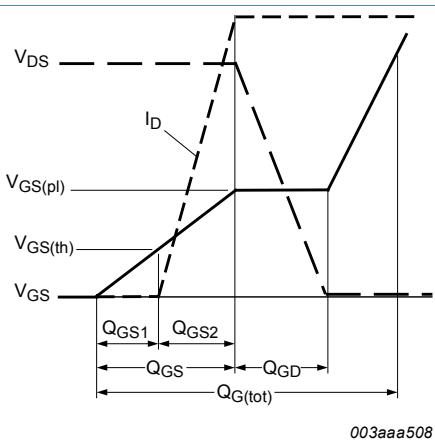
**Fig. 12. Drain-source on-state resistance as a function of drain current; typical values**

$T_j = 25^\circ C$

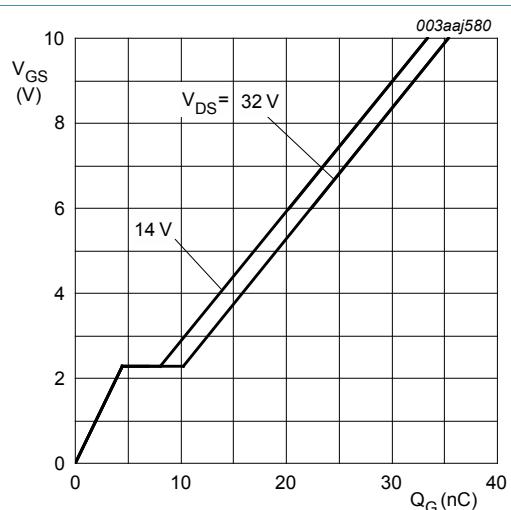


**Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature**

$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ C)}$$

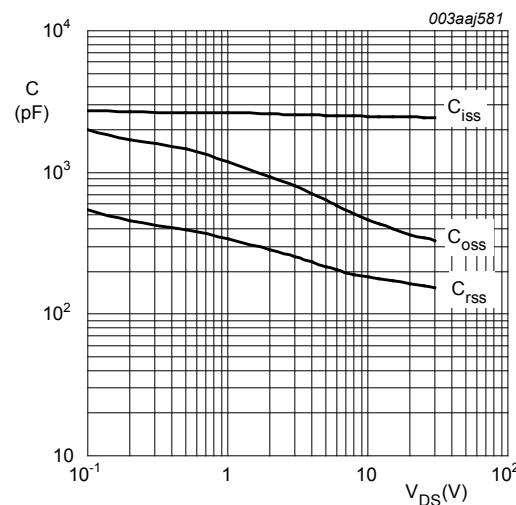


**Fig. 14. Gate charge waveform definitions**



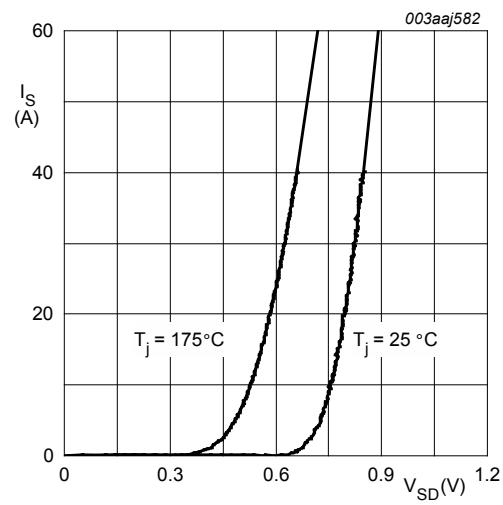
**Fig. 15. Gate-source voltage as a function of gate charge; typical values**

$T_j = 25^\circ C; I_D = 10 A$



**Fig. 16.** Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

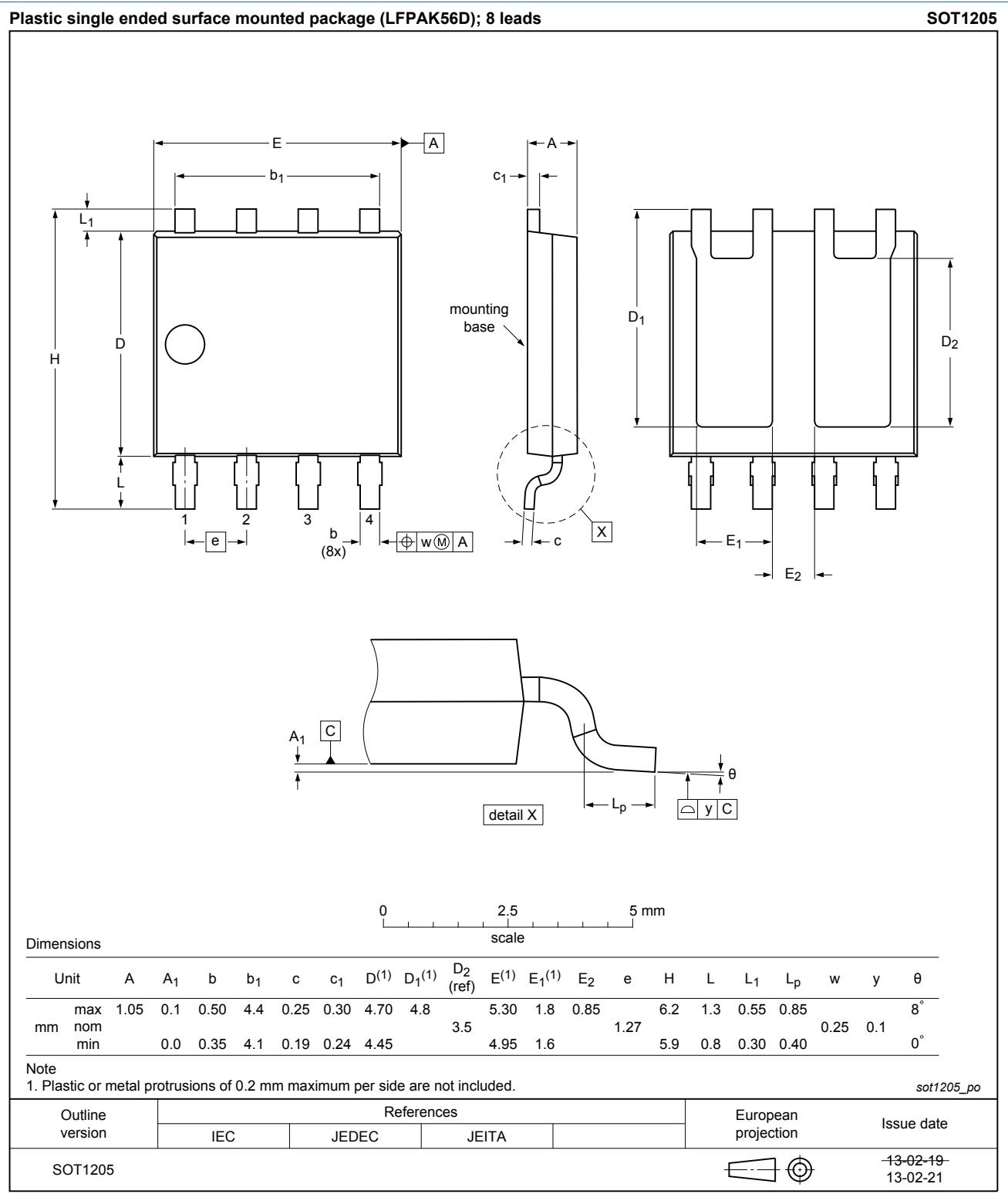
$V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



**Fig. 17.** Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$V_{GS} = 0 \text{ V}$

## 11. Package outline



## 12. Legal information

### 12.1 Data sheet status

| Document status [1][2]         | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

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- [2] The term 'short data sheet' is explained in section "Definitions".
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Date of release: 23 April 2013

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